Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1-9. (Canceled)

10. (Currently Amended) A method for producing a single crystal by Czochralski method by pulling a seed crystal from a raw material melt, comprising:

immersing a seed crystal into a raw material melt; and

growing a single crystal by rotating and pulling the seed crystal,

~~wherein~~ wherein:

the single crystal is pulled with controlling a value of V/G ($mm^2/K \cdot min$) within a determined range; and ~~range,~~

the range of a value of V/G ($mm^2/K \cdot min$), including a desired defect region and/or a desired defect-free region, is determined according to Tmax (°C); ~~Tmax (°C),~~ wherein:

V(mm/min) is the single crystal pulling rate of pulling a single crystal;

G (K/mm) is a temperature gradient at a solid-liquid interface, in a range of ~~the~~ a melting point of the raw material and 1400°C; ~~and~~

Tmax (°C) is the highest temperature of the raw material melt at an interface between a quartz crucible inner wall and a raw material ~~melt.~~melt; and

the range of a value of V/G ($mm^2/K \cdot min$) is selected from a group consisting of:

from $-0.000724\ [mm^2/(°C \cdot K \cdot min)] \times Tmax\ (°C) + 1.31\ (mm^2/K \cdot min)$ to less than $-0.000724\ [mm^2/(°C \cdot K \cdot min)] \times Tmax\ (°C) + 1.38\ (mm^2/K \cdot min)$;

$-0.000724\ [mm^2/(°C \cdot K \cdot min)] \times Tmax\ (°C) + 1.38$

$(mm^2/K \cdot min)$ or more; and

from $-0.000724\ [mm^2/(°C \cdot K \cdot min)] \times Tmax\ (°C) + 1.31$

$(mm^2/K \cdot min)$ to $-0.000724\ [mm^2/(°C \cdot K \cdot min)] \times Tmax\ (°C) + 1.35\ (mm^2/K \cdot min)$.

11-13. (Canceled)

14. (Previously Presented) The method for producing a single crystal according to Claim 10, wherein the single crystal is pulled with the Tmax (°C) being in a range of 1560 °C or less.

15-17. (Canceled)

18. (Previously Presented) The method for producing a single crystal according to Claim 10, wherein, at least, the Tmax (°C) is changed by providing a heat insulating material between the crucible containing the raw material melt and a heater provided so as to surround the crucible, or by providing a heat insulating material below the crucible.

19-21. (Canceled)

22. (Previously Presented) The method for producing a single crystal according to Claim 14, wherein, at least, the Tmax (°C) is changed by providing a heat insulating material between the crucible containing the raw material melt and a heater provided so as to surround the crucible, or by providing a heat insulating material below the crucible.

23-25. (Canceled)

26. (Previously Presented) The method of producing a single crystal according to Claim 10, wherein a silicon single crystal is pulled as the single crystal.

27. (Previously Presented) The method of producing a single crystal according to Claim 10, wherein a single crystal with a diameter of 200mm or more is pulled as the single crystal.

28. (Canceled)